

MITSUBISHI LSIs M5G1400P

1400-BIT (100-WORD BY 14-BIT) ELECTRICALLY ALTERABLE ROM

DESCRIPTION

The M5G1400P is a serial input/output 1400-bit electrically erasable and reprogrammable ROM organized as 100 words of 14 bits, and fabricated using MNOS technology. Data and addresses are transferred serially via a one-bit bidirectional bus.

FEATURES

- Word-by-word electrically alterable
- Non-volatile data storage: 10 years (min)
- Write/erase time: 20ms/word
- Single 35V power supply
- Number of erase-write cycles: 10^5 times (min)
- Number of read access unrefreshed: 10^9 times (min)

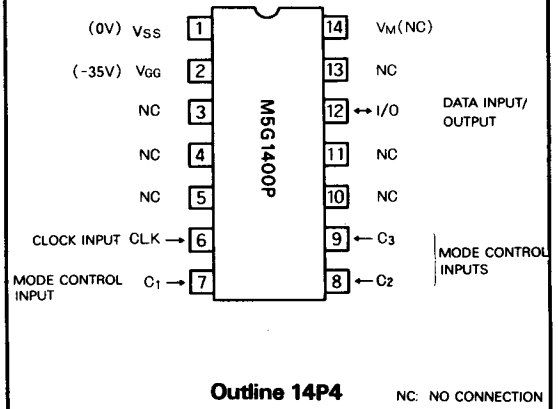
APPLICATION

Non-volatile channel memories for electronic tuning systems and field-reprogrammable read-only memory systems

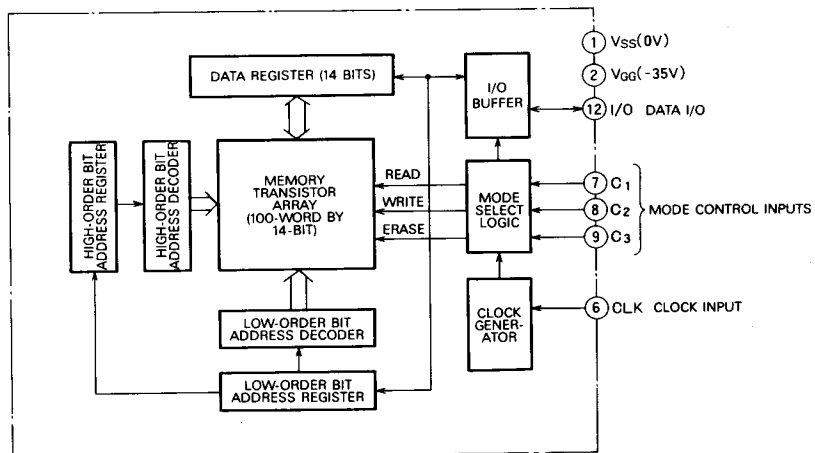
FUNCTION

The address is designated by two consecutive one-of-ten-coded digits. Seven modes—accept address, accept data, shift data output, erase, write, read, and standby—are all selected by a 3-bit code applied to C₁, C₂, and C₃. Data is stored by internal negative writing pulses that selectively tunnel charges into the SiO₂-Si₃N₄ interface of the gate insulators of the MNOS memory transistors.

PIN CONFIGURATION (TOP VIEW)



BLOCK DIAGRAM



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PIN DESCRIPTION

Pin	Name	Functions
I/O	I/O	In the accept address and accept data modes, used for input. In the shift data output mode, used for output. In the standby, read, erase and write modes, this pin is in a floating state.
V _M	Test	Used for testing purposes only. It should be left unconnected during normal operation.
V _{SS}	Chip substrate voltage	Normally connected to ground.
V _{GG}	Power supply voltage	Normally connected to -35V.
CLK	Clock input	14kHz timing reference. Required for all operating modes. High-level input is possible during standby mode.
C ₁ - C ₃	Mode control input	Used to select the operation mode.

OPERATION MODES

C ₁	C ₂	C ₃	Functions
H	H	H	Standby mode. The contents of the address registers and the data register remain unchanged. The output buffer is held in the floating state.
H	H	L	Not used.
H	L	H	Erase mode. The word stored at the addressed location is erased. The data bits after erasing are all low-level.
H	L	L	Accept address mode. Data presented at the I/O pin is shifted into the address registers one bit with each clock pulse. The address is designated by two one-of-ten-coded digits.
L	H	H	Read mode. The addressed word is read from the memory into the data register.
L	H	L	Shift data output mode. The output driver is enabled and the contents of the data register are shifted to the I/O pin one bit with each clock pulse.
L	L	H	Write mode. The data contained in the data register is written into the location designated by the address registers.
L	L	L	Accept data mode. The data register accepts serial data from the I/O pin one bit with each clock pulse. The address registers remain unchanged.

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ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Conditions	Ratings	Unit
V _{GG}	Supply voltage	With respect to V _{SS}	0.3 ~ -40	V
V _I	Input voltage		0.3 ~ -20	V
V _O	Output voltage		0.3 ~ -20	V
T _{stg}	Storage temperature		-65 ~ 150	°C
T _{opr}	Operating temperature		-10 ~ 70	°C

RECOMMENDED OPERATING CONDITIONS (T_a = -10 ~ 70°C, unless otherwise noted.)

Symbol	Parameter	Limits			Unit
		Min	Nom	Max	
V _{GG}	Supply voltage	-32.2	-35	-37.8	V
V _{SS}	Supply voltage (GND)		0		V
V _{IH}	High-level input voltage	V _{SS} -1		V _{SS} +0.3	V
V _{IL}	Low-level input voltage	V _{SS} -15		V _{SS} -8	V

Note 1:
The order of V_{SS} V_{GG} with on or off.
With on, V_{GG} is turned on after V_{SS} is done.
With off, V_{SS} is turned off after V_{GG} is done.

ELECTRICAL CHARACTERISTICS (T_a = -10 ~ 70°C, V_{GG} = -35V ± 8%, unless otherwise noted.)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
V _{IH}	High-level input voltage		V _{SS} -1		V _{SS} +0.3	V
V _{IL}	Low-level input voltage		V _{SS} -15		V _{SS} -8	V
I _{IL}	Low-level input current	V _I = -15V			± 10	μA
I _{OZL}	Off-state output current, low-level voltage applied	V _O = -15V			± 10	μA
V _{OH}	High-level output voltage	I _{OH} = -200μA	V _{SS} -1			V
V _{OL}	Low-level output voltage	I _{OL} = 10μA			V _{SS} -12	V
I _{GG}	Supply current from V _{GG}	I _O = 0μA	5.5	8.8		mA

Note 2: Typical values are at T_a = 25°C and nominal supply voltage.

TIMING REQUIREMENTS (T_a = -10 ~ 70°C, V_{GG} = -35V ± 8%, unless otherwise noted.)

Symbol	Parameter	Alternative symbols	Test conditions	Limits			Unit
				Min	Typ	Max	
f(φ)	Clock frequency	fφ		11.2	14	16.8	kHz
D(φ)	Clock duty cycle	Dφ		30	50	55	%
t _w (w)	Write time	t _w		16	20	24	ms
t _w (E)	Erase time	t _e		16	20	24	ms
t _r , t _f	Risetime, falltime	t _r , t _f				1	μs
t _{su} (c-φ)	Control setup time before the fall of the clock pulse	t _{CS}			0		ns
t _h (φ-c)	Control hold time after the rise of the clock pulse	t _{CH}			0		ns

SWITCHING CHARACTERISTICS (T_a = -10 ~ 70°C, V_{GG} = -35V ± 8%, unless otherwise noted.)

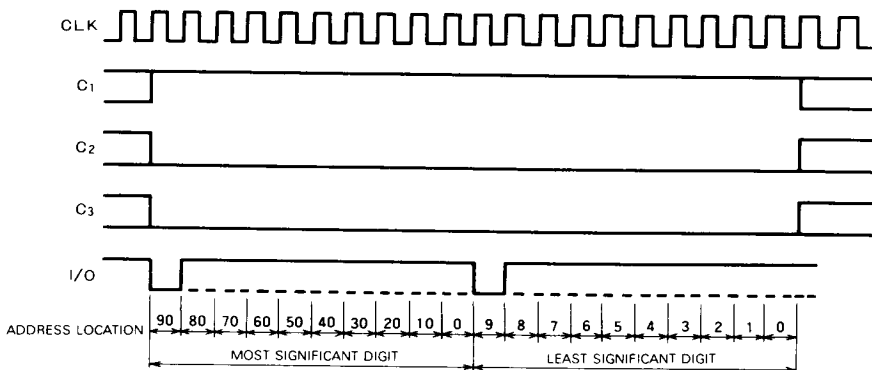
Symbol	Parameter	Alternative symbols	Test conditions	Limits			Unit
				Min	Typ	Max	
t _a (c)	Read access time	t _{pw}	C _L = 100pF V _{OH} = V _{SS} - 2V V _{OL} = V _{SS} - 8V			20	μs
t _s	Unpowered nonvolatile data retention time	T _S	N _{EW} = 10 ⁴ , t _w (w) = 20ms t _w (E) = 20ms	10			Year
		T _S	N _{EW} = 10 ⁵ , t _w (w) = 20ms t _w (E) = 20ms	1			
N _{EW}	Number of erase/write cycles	N _w		10 ⁵			Times
N _{RA}	Number of read access unrefreshed	N _{RA}		10 ⁸			Times
t _{dv}	Data valid time	t _{pw}				20	μs



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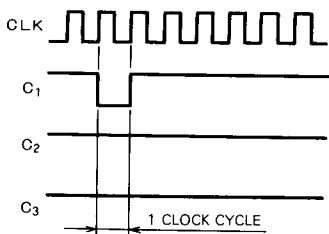
TIMING DIAGRAM

Accept Data Mode

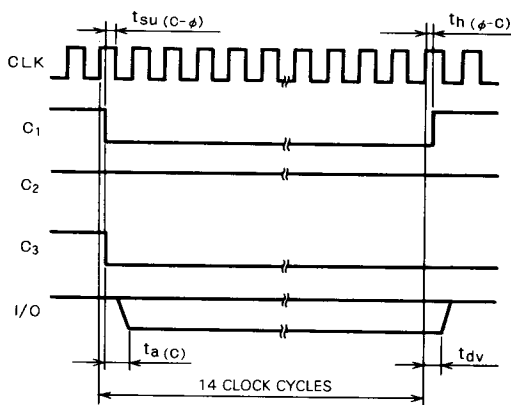


Note 3: The address is designated by two one-of-ten-coded digits. The figure shows designation of the address 99.

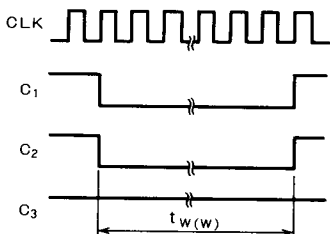
Read Mode



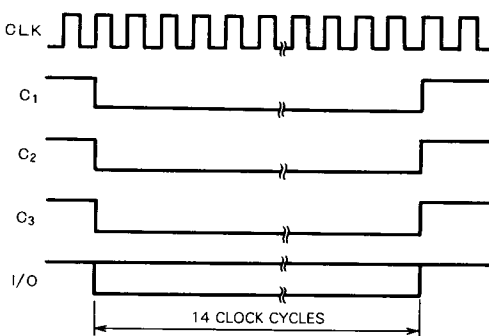
Shift Data Output Mode



Write Mode



Accept Data Mode



Erase Mode

